

Exciton condensate at total filling factor 1 in Corbino 2D electron bilayers

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Magneto-transport and drag measurements on a quasi-Corbino 2D electron bilayer at the systems total filling factor 1 ($\nu_T=1$) reveal a drag voltage that is equal in magnitude to the drive voltage as soon as the two layers begin to form the expected $\nu_T=1$ exciton condensate. The identity of both voltages remains present even at elevated temperatures of 0.25 K which contrasts markedly to the behavior observed in Hall bars. The conductance in the current carrying layer vanishes only in the limit of strong coupling between the two layers and at $T \rightarrow 0$ K which suggests the presence of an excitonic circular current.

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When two closely spaced two-dimensional electron systems (electron bilayer) are exposed to a perpendicular magnetic field B so that each layer has a filling factor close to $1/2$ and the relative distance between interlayer electrons, parameterized by the ratio d/l_B (d : layer separation, $l_B = \sqrt{\hbar/eB} = 1/\sqrt{2\pi n_T}$: magnetic length with n_T as the total density), is sufficiently small, a new quantum Hall (QH) state characterized by the total filling factor 1 ($\nu_T=1$) can be observed. Both theoretically and experimentally it is found that this novel state in bilayers occurs at a d/l_B ratio of less than ≈ 2 [1, 2]. In the limit of comparably small tunneling, its origin is dominated by Coulomb interactions, where the electrons in the two layers form a strongly correlated many-body state to minimize their exchange energy. In this state and in the low temperature limit, spontaneous interlayer phase coherence develops, driving all electrons in a quantum mechanical superposition of the layer eigenstates sharing the same macroscopic phase ϕ [3, 4]. However, the predicted Kosterlitz-Thouless type of phase-transition [12] has not yet been unequivocally demonstrated in experiment. After a particle-hole transformation that changes the sign of the interactions from repulsive to attractive, this state can be regarded as an excitonic condensate, where each electron is bound to a “vacant state” in the opposite layer. Interlayer drag experiments, where a constant current is passed through one of the layers (“drive layer”) and the induced longitudinal and transverse voltage drop in the other layer (“drag layer”) is measured [2], have revealed a Hall drive and drag which approaches a quantized value of h/e^2 at $\nu_T = 1$ in a temperature-activated fashion. The quantization of the Hall drag is an indirect indication of a superfluid mode of excitons [5], which can be viewed as either an uniform flow of interlayer excitons or as a counter flow of electrons in the opposite layers.

In standard Hall bars the occurrence of the ordinary integer QH effect with the vanishing of the longitudinal

resistance and the quantization of the Hall resistance can be explained in terms of one-dimensional (dissipationless) edge channels [6, 7]. However, in the case of the $\nu_T = 1$ and its associated superfluid transport mode, it cannot be ruled out from the Hall bar data that a dissipationless quasi-particle current at the sample edges is responsible for the observed effects [8].

In this Letter, we report on interlayer drag measurements on a *quasi*-Corbino electron bilayer with independent contacts to both layers. An *ideal* Corbino structure allows direct measurement of the conductivity σ_{xx} in contrast to the common Hall bar geometry where the resistivities are measured. Due to the absence of sample edges connecting source and drain contacts in a ring, a current can be driven selectively through the bulk of the $\nu_T = 1$ system, when the interlayer tunneling is negligible. Such a situation can be achieved either at high temperatures or at relatively large $d/l_B (\leq 2)$ where the bulk conductance becomes comparable to the tunneling conductance. We observe that at $\nu_T = 1$ a voltage develops in the drag layer that equals in sign and magnitude the voltage across the drive layer. In striking contrast to previous results from Hall bars, we find that the identity of the drag and drive voltages is maintained up to high temperatures or large d/l_B where the single layer current flow shows nearly no trace of the $\nu_T = 1$ QH effect. On the other hand, at low temperatures, drive and drag voltage remain identical and the drive current nearly vanishes, creating a situation where the bulk resistance and the interlayer resistance are of the same order of magnitude. The Corbino experiments thus open a new venue to explore the bulk property of the $\nu_T = 1$ system.

Our two-dimensional (2D) electron bilayer is confined in two 19-nm GaAs quantum wells, separated by a 9.9 nm superlattice barrier composed of alternating layers of AlAs (1.70 nm) and GaAs (0.28 nm). Each quantum well has an intrinsic electron density of about $4.3 \times 10^{14} \text{ m}^{-2}$ and a low-temperature mobility of 67 (45) m^2/Vs

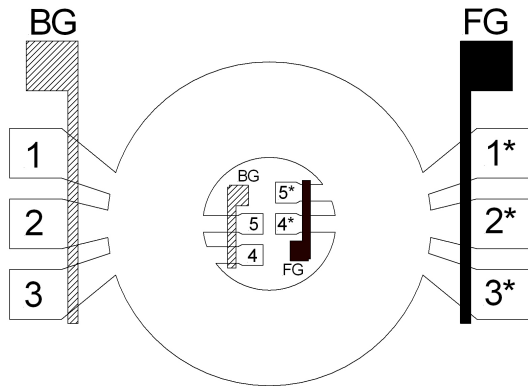


FIG. 1: Schematic view of the Corbino geometry used in this experiment. Application of appropriate voltages to the back gates (marked as "BG") and front gates ("FG") will lead to contact separation, i.e. contacts 1 through 5 will connect to the upper quantum well and 1* through 5* to the lower one.

for the upper (lower) quantum well (measured on a Hall bar fabricated from the same wafer). Since the ideal Corbino geometry is not compatible with the selective-depletion technique [9, 10] for independently contacting each layer, we instead employ a quasi-Corbino geometry with four contacts arms attached to each ring as depicted in Fig. 1. The back gates were patterned *ex situ* from a Si-doped GaAs epilayer before growing an insulating GaAs/AlGaAs superlattice and the bilayer on top. Electrical isolation between the two layers is achieved by applying appropriate negative voltages to the buried back gates and metallic front gates crossing the contact arms. One set of contacts can then be used to pass a current and another one to measure the voltage across the ring. The densities in each layer can be adjusted independently by using another set of front and back gates (not shown) covering the active region of the Corbino ring including the ring edges.

Below we present data from two samples from the same wafer which show essentially the same behavior. Sample A consists of a quasi-Corbino ring with an outer diameter of $d_O = 600 \mu\text{m}$ and a ring width of $w = 140 \mu\text{m}$, while sample B is characterized by $d_O = 780 \mu\text{m}$ and $w = 230 \mu\text{m}$. For all samples interlayer tunneling is small; the interlayer resistance (at zero magnetic field and 0.25 K) is of the order $10^7 - 10^8 \Omega$. Transport measurements were performed by using a standard lock-in technique with the sample mounted at the cold finger of a dilution refrigerator or a ^3He system. For all measurements the electron densities in the two layers were adjusted to be equal. A small excitation voltage ($60\text{-}65 \mu\text{V}$, $3\text{-}5 \text{Hz}$ [17]) was applied radially across one layer (the drive layer) through an isolation transformer and the induced current through this layer was measured with a small resistance

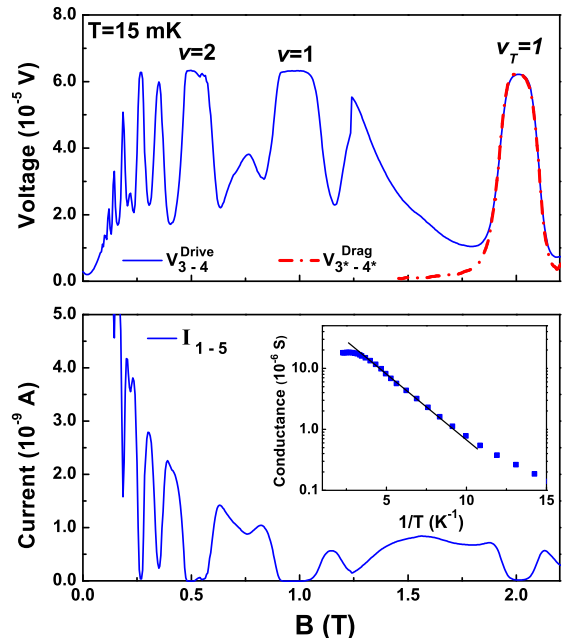


FIG. 2: Top panel: Measured drive (solid line) and drag (dash-dot line) voltages at $T_{\text{bath}}=15 \text{ mK}$ on sample B. The (integer) filling factors $\nu \leq 2$ and $\nu_T = 1$ ($d/l_B=1.62$) are labeled. Bottom panel: Measured current in the drive layer. The inset plots the temperature dependence of the radial conductance G ; the line is a fit using $G \propto \exp(-E_{\text{gap}}/T)$.

connected in series. The voltage dropping over the drive layer changes in response to the current that oscillates as a function of the magnetic field. For that reason, the voltage across the drive layer was monitored using a separate pair of contacts in a quasi four-terminal geometry together with the induced voltage in the drag layer. This excludes also the effects of the finite resistances of the ohmic contacts and the contact arms. The measurements were reproducible upon interchanging contacts and upon interchanging drive and drag layer.

We start by showing data at low temperatures. Fig 2 presents data at $T_{\text{bath}} = 15 \text{ mK}$ on sample B. The bottom and top panel plot the measured current in the drive layer and the corresponding drive and drag voltages as a function of the magnetic field. The electron densities in the two layers were adjusted to be equal, producing a total density of $4.8 \times 10^{14} \text{ m}^{-2}$. Below 1.5 T, the current oscillates reflecting the varying filling factors and integer QH states. At total filling factor 1 which occurs here at 2.0T, we observe a strong minimum in the current. As a result, the voltage drop over the drive layer almost equals the source voltage (top panel). The vanishing conductance at $\nu_T = 1$ is actually in common with the ordinary QH effects at lower magnetic fields corresponding to integer

fillings of the individual layers, where the Corbino ring is in an incompressible state, i.e. where the Hall current flows along circular equipotential lines. More interesting is the large drag voltage that develops over the region of the correlated $\nu_T = 1$ phase, with the sign and magnitude identical to that of the drive layer. In previous drag experiments using Hall bars, identical Hall voltages in the drag and drive layers were considered to be signaling the underlying excitonic superfluidity. Our observation of equal voltages in the two layers is intriguing to the effect that, different from the case of the Hall drag in Hall bars, in a Corbino geometry the large drag voltage exists *in the absence of the external driving current*. Our findings suggest that the drive voltage sets up a circling current which by the excitonic coupling produces a current of the same size in the drag layer leading to identical voltages across both layers. Even though there is no direct access to the azimuthal component of the current, the well-established model of electron-hole pairing around $\nu_T = 1$ implies such a transport mode in Corbino bilayers. Supported is that notion by the fact that the contacts of the drag layer in our geometry are located at the opposite side of the ring, i.e. approximately 1 mm away from the contacts of the drive layer.

In a different scenario, owing to the drive layer's impedance of several M Ω at total filling factor 1 and lowest temperatures, tunneling between the edges might become important, resulting in the observed voltage drop across the drag layer. However, to observe nearly identical voltages, the interlayer resistance must be less than about 100k Ω , which is inconsistent with our interlayer tunneling experiments that indicate an interlayer resistance of several M Ω instead [18]. Also, a weak barrier should create a comparable drag voltage at all other filling factors which was not observed.

Fig. 3 plots data taken at a temperature of $T=0.25$ K on sample A. The densities in both layers are still equal but reduced to a total electron density of approximately $4.2 \times 10^{14} \text{ m}^{-2}$. Now $\nu_T = 1$ occurs at $B=1.76$ T which corresponds to $d/l_B = 1.49$. At 0.25 K the minimum in the current has almost entirely disappeared (bottom panel). Nonetheless, there is still a sizeable peak in the drive voltage at $\nu_T = 1$ (solid line in the top panel). Surprisingly, the voltage over the drag layer (dash-dot line) also displays a peak *with the same amplitude*. This constitutes the direct proof that the strong interlayer correlation remains present at these elevated temperatures. In Hall bar bilayers, on the other hand, identical voltages, i.e. the quantization of the Hall resistance to h/e^2 , are only observable at low temperatures and low d/l_B ratios when the $\nu_T = 1$ QH state is fully developed (e.g. see Ref. [2]) and the whole sample is incompressible. The resilience of the $\nu_T = 1$ QH state to increasing temperatures in Corbino 2D electron bilayers is a behavior reminiscent of results obtained on bilayer 2-dimensional hole gas samples [11]. Whether this is owing to the re-

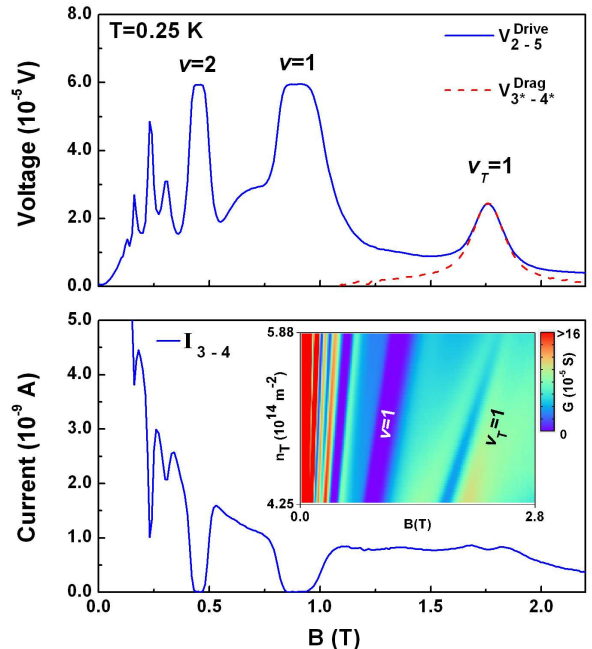


FIG. 3: Top panel: Drive (solid line) and drag (dash-dot line) voltage versus the magnetic field at $T = 0.25$ K measured on sample A. Bottom panel: The current in the drive layer measured simultaneously. The inset illustrates the conductance G of the drive layer as a function of the magnetic field and the total density. Clearly visible is how the conductance at $\nu_T = 1$ decreases as the total density n_T is reduced.

ported interlayer leakage or to the larger effective mass of the holes is beyond the scope of this Letter.

We find that the ratio of both voltages remains 1 until d/l_B approaches a critical limit. We have traced the drag and drive voltages for a number of different (but matched) total densities at 0.25 K. The results are summarized in Fig. 4 which plots drag and drive voltage at $\nu_T=1$ versus d/l_B . At 0.25 K, the identity of both drag and drive voltages can be tracked up to a d/l_B ratio of about 1.65 where the $\nu_T = 1$ QH state is collapsing owing to thermal fluctuations. For $d/l_B > 1.65$ small peaks of different amplitude can be observed as illustrated in the inset.

At some finite temperature, the collapse of the excitonic condensate at $\nu_T = 1$ in the bilayer can be observed. For sample B and temperatures below 0.25 K, the conductance $G=I/V$ is well described by thermal activation, i.e. $G \propto \exp(-E_{gap}/T)$, with an activation energy gap of approximately 0.5 K as shown in the inset of Fig 2. The magnitude of the extracted energy gap is in good agreement with earlier reports on comparable double quantum well structures [2, 13, 14, 15], where the activation energy was extracted from measurements of the temperature de-

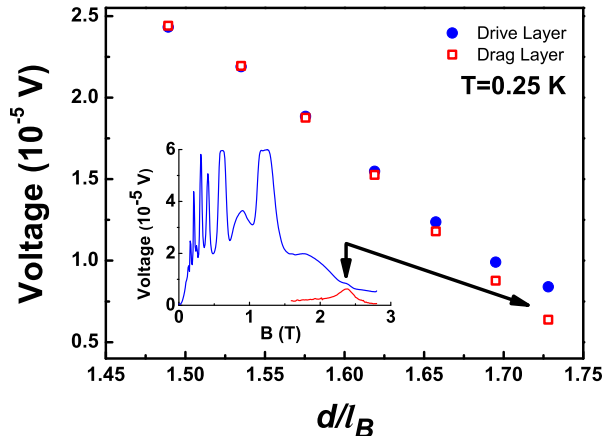


FIG. 4: Drive (solid dots) and drag (open dots) voltages at $\nu_T = 1$ versus the parameter d/l_B at $T_{bath} = 0.25$ K. Above $d/l_B = 1.65$, the amplitudes of drive and drag voltage at total filling factor 1 diverge. The inset shows the corresponding field sweep for the last pair of points at $d/l_B = 1.73$.

pendence of the longitudinal resistance in Hall bars.

In a theoretical Letter, Stern and Halperin [16] suggested that the electron bilayer system at high d/l_B ratios is composed of puddles of strong interlayer correlation incorporated in the compressible fluids of the individual layers. Their model, albeit addressing specifically Hall bar geometries, appears to be connected with our observations as well. As long as these puddles are small in number and/or unrelated, a sizeable current could flow through the bulk between source and drain contacts. As d/l_B is decreased their number and/or size will increase until they eventually percolate, while the current through the bulk slowly diminishes. The smooth transition we observe in Corbino samples from a compressible to a nearly fully incompressible state upon decreasing the temperature and/or the parameter d/l_B appears to signify such a percolation.

In conclusion, we have conducted interlayer drag experiments on quasi-Corbino electron bilayers. At the lowest temperature and strong coupling the ratio of drag and drive voltages is 1 while the conductance in the drive layer vanishes. Our data suggest the existence of a circulating current in the drive layer which by interlayer corre-

lation triggers a current of the same size in the drive layer. At elevated temperatures, the identity of both voltages is still present, unlike what would have been expected from prior Hall bar experiments.

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